Docket No.: VISH-8728

closure Statement Transmittal

I hereby certify that this transmittal of the below described document is being deposited with the United States Postal Service in an envelope bearing First Class Postage and addressed to the Commissioner of Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on the below date of deposit.

Date of Deposit:

11/8/05

Name of Person Making the Deposit:

Lux Costillo

Signature of the Person Making the Deposit:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s):

Pattanayak et al.

Application No.:

10/726,922

Group Art Unit:

2815

Filed:

December 2, 2003

Examiner:

Fenty, Jesse, A.

Confirmation No:

8797

Title:

CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT

TRANSISTOR

Commissioner of Patents

P. O. Box 1450

Alexandria, VA 22313-1450

Sir:

Information Disclosure Statement Transmittal

Transmitted herewith is the following:

Formal drawings, totaling

sheets. Informal drawings, totaling sheets.

X Certification for PTO Consideration

X Information Disclosure statement (1 sheet)

Information Disclosure statement and late filing fee

X Form 1449

Petition for Extension of Time

X Other:

Under 37 C.F.R 1.97 (c)

Fee Calculation (for other than a small entity)					
Fee Items	Fee Rate	Total			
Petition for Extension of Time (fee calculated elsewhere \$.00					
Information Disclosure Statement, late filing \$180.00					
Other: Peittion Under 37 C.F.R 1.97 (c)					
Total Fees					

PAYMENT OF FEES

- 1. The full fee due in connection with this communication is provided as follows:
- [] The Commissioner is hereby authorized to charge any additional fees associated with this communication or credit any overpayment to Deposit Account No.: 23-0085.

A <u>duplicate copy</u> of this authorization is enclosed.

_0000028_10726922 11/16/2005 MBERHE

[X] A check in the amount of \$180.00

01 FC:1806

180:00 OP

Charge any fees required or credit any overpayments associated with this filing to Deposit Account No.: 23-0085.

Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP

Two North Market Street, Third Floor San Jose, California 95113 (408) 938-9060

Customer No: 000041066

Respectfully submitted,

Anthony C. Murabito Reg. No. 35,295



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No.: VISH-8728 I hereby certify that this transmittal of the below described document is being deposited with the United States Postal Service in an envelope bearing First Class Postage and addressed to the Commissioner for Patents P.O. Box 1450, Alexandria, VA 22313-1450, on the below date of deposit. Date of Name of Person Signature of the Person 11/8/05 Making the Deposit: Making the Deposit: Deposit: Pattanayak et al. Inventor(s): 10/726,922 **Group Art Unit:** 2815 Application No.: December 2, 2003 Filed: Examiner: Fenty, Jesse, A. 8797 Confirmation No: CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT Title: TRANSISTOR Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 Certification for PTO Consideration of an Information Disclosure Statement (Under 37 CFR §1.97) Consideration of the enclosed Information Disclosure Statement is requested. 1. This certification is being made for this information disclosure statement [X] accompanying this certification [] Filed _____ 2. I hereby certify that: X Each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the statement. No item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart application, or, to the knowledge of the person signing certification after making reasonable inquiry, was known to any individual designated in §1.56(c) more than three months prior to the filing of the statement. 3. The person making this certification is [X] a person who is substantively involved in the preparation or prosecution of the application, and who is associated with the inventor, with the assignee, or with anyone to whom there is an obligation to assign the application (37 C.F.R. 1.56 (c)) and who signs below. [] the inventor(s) who signs below [] the practitioner who signs below on the basis of the information: [] supplied by the inventors

[] supplied by an individual designated in § 1.56(c)

[] in the practitioners file

Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP

Two North Market Street, Third Floor San Jose, California 95113 (408) 938-9060 Customer No: 000041066

Respectfully submitted,

Date: 11/3/2005

Anthony C. Murabito

Reg. No. 35,295



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No.: VISH-8728

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Date of 11/2 / N

Deposit:

Name of Person
Making the Deposit:

LUZ

Costillo

Signature of the Person Making the Deposit:

of Castill

Inventor(s):

Pattanayak et al.

Application No.:

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8797

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TRANSISTOR

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT BEFORE MAILING DATE OF EITHER A FINAL ACTION OR NOTICE OF ALLOWANCE § (37 C.F.R. 1.97(c))

TIME OF TRANSMITTAL OF ACCOMPANYING INFORMATION DISCLOSURE STATEMENT

- The information disclosure statement transmitted herewith is being filed *after* three months of the filing date of this national application or the date of entry of the national stage as set forth in § 1.491 in an international application or after the mailing date of the first Office action on the merits, whichever event occurred last but *before* the mailing date of either:
 - (1) a final action under § 1.113 or
 - (2) a notice of allowance under § 1. 311,

which ever occurs first

STATEMENT OR FEE

- 2. Accompanying this transmittal is
 - A. Para a statement as specified in 37 C.F.R. § 1.97(e).

or

B. The fee set forth in 37 C.F.R. § 1.17(p) for submission of an information disclosure statement under § 1.97(c). (\$180.00).

FEE PAYMENT

3. Applicant elects the option to pay the fee set forth in 37 C.F.R. 1.17(p) for submission of an information disclosure statement under 1.97(c) (\$180.00).

Fee due \$ 180.00

METHOD OF PAYMENT OF FEE

4. [X] Attached is a check for \$180.00.

Charge account 23-0085 \$180.00

A duplicate of this petition is attached

If any additional petition fees are due, please charge Account 23-0085

Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP Two North Market Street, Third Floor

San Jose, California 95113 (408) 938-9060 Customer No: 000041066

Respectfully submitted,

Date:

Anthony C. Murabito

Reg. No. 35,295



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No.: VISH-8728

Pattanayak et al.

Application No.:

10/726,922

Group Art Unit:

2815

Filed:

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Examiner:

Fenty, Jesse, A.

Confirmation No:

8797

Title:

CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT

TRANSISTOR

Commissioner of Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Information Disclosure Statement Submitted Pursuant to 37 C.F.R. 1.97(b)

The citations referenced herein, copies attached, may be material to the examination of the above-identified application and are, therefore, submitted in compliance with the duty of disclosure as defined in 37 C.F.R. 1.56. The Examiner is requested to make these citations of official record in the application.

This Information Disclosure Statement submitted in accordance with 37 C.F.R. 1.97(b) is not to be construed as a representation that a search has been made, that additional items material to the examination of this application do not exist, or that any one or more of these citations constitute prior art under 35 U.S.C. 102.

The Examiner's attention is respectfully directed to the following U.S. Patents:

Publ./Pat. No.

Pat. Title

Grant Date

2004/0195618

INSULATED GATE SEMICONDUCTOR DEVICE

Oct. 7, 2004

6,838,730

SEMICONDUCTOR DEVICE

Jan. 4, 2005

Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP

Two North Market Street, Third Floor San Jose, California 95113 (408) 938-9060

11/16/2005 MBERHE

00000028 10726922

01 FC:1806

180.00 OP

Customer No: 000041066

Respectfully submitted.

Date:

Anthony C. Murabito

Reg. No. 35,295



Attorney Docket No.: VISH-8728

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application

Inventor(s):

Pattanayak et al.

Application No.:

10/726,922

Group Art Unit:

2815

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December 2, 2003

Examiner:

Fenty, Jesse, A.

Confirmation No:

8797

Title:

CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT

TRANSISTOR

Form 1449

U.S. Patent Documents

Examiner						Sub-	Filing
Initial	No.	Publ.Patent No.		Patentee	Class	class	Date
	Α	2004/0195618	10/7/04	Saito et al.	257	330	6/18/03
	В	6,838,730	1/14/05	Kawaguchi et al.	257	331	2/20/04
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	K						

Foreign Patent or Published Foreign Patent Application

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Examiner		Document	Publication	Country or		Sub-	Translation	
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
	L							
	М							
	N							
	0							
	Р							
	Q							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	R	
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.